

Gyro Readout Equivalent Circuit (for a single tine)

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$\vec{F}_c = m\vec{a}_c = m \cdot (2\vec{\dot{x}}_d \times \vec{\Omega})$

Noise Sources

- i_f^2 ← noise due to
- v_{ia}^2
- i_{ia}^2
- parallel-plate sensor electrode
- noise associated with
- Noise of the op amp (equivalent input noise generator)

Gyro Sense Element Output Circuit **Signal Conditioning Circuit (Transresistance Amplifier)**

- Easiest to analyze if all noise sources are summed at a common node

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Minimum Detectable Signal (MDS)

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- Minimum Detectable Signal (MDS):** Input signal level when the signal-to-noise ratio (SNR) is equal to unity

We will do this!

Sensed Signal → **Sensor** (Sensor Scale Factor, Sensor Noise) → **Signal Conditioning Circuit** (Circuit Gain, Circuit Output Noise) → **Output**

Includes desired output plus noise

$N_0 = A^2 \Delta f$

- The sensor scale factor is governed by the sensor type
- The effect of noise is best determined via analysis of the equivalent circuit for the system

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Move Noise Sources to a Common Point

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- Move noise sources so that all sum at the input to the amplifier circuit (i.e., at the output of the sense element)
- Then, can compare the output of the sensed signal directly to the noise at this node to get the MDS

Alternatively, can sum noise here. (Module does.)

Sensed Signal → **Sensor** (Sensor Scale Factor, Sensor Noise) → **Signal Conditioning Circuit** (Circuit Gain, Circuit Input-Referred Noise) → **Output**

Includes desired output plus noise

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Equivalent Input-Referred Voltage and Current Noise Sources

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Equivalent Input v, i Noise Generators

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- Take a noisy 2-port network and represent it by a noiseless network with input v and i noise generators that generate the same total output noise

- Remarks:
 - Works for linear time-invariant networks
 - v_{eq} and i_{eq} are generally correlated (since they are derived from the same sources)
 - In many practical circuits, one of v_{eq} and i_{eq} dominates, which removes the need to address correlation
 - If correlation is important \rightarrow easier to return to original network with internal noise sources

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Calculation of v_{eq}^2 and i_{eq}^2

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a) To get v_{eq}^2 for a two-port:

- Short input, find v_{0I}^2 (or i_{0I}^2)
- For eq. network, short input, find v_{0II}^2 (or i_{0II}^2)

$$\frac{f(v_{eq}^2)}{f(v_{0I}^2)} = \frac{f(v_{eq}^2)}{f(v_{0II}^2)}$$

- Set $v_{0I}^2 = v_{0II}^2 \rightarrow$ solve for v_{eq}^2 (or $i_{0I}^2 = i_{0II}^2$)

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Calculation of v_{eq}^2 and i_{eq}^2 (cont)

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b) To get i_{eq}^2 for a 2-port:

- Open input, find v_{0I}^2 (or i_{0I}^2)
- Open input for eq. circuit, find v_{0II}^2 (or i_{0II}^2)
- Set $v_{0I}^2 = v_{0II}^2 \left(\frac{i_{eq}^2}{i_{0I}^2} \right) \rightarrow$ solve for i_{eq}^2 (or $i_{0I}^2 = i_{0II}^2 \left(\frac{i_{eq}^2}{i_{0I}^2} \right)$)

- Once the equivalent input-referred noise generators are found, noise calculations become straightforward as long as the noise generators can be treated as uncorrelated

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Cases Where Correlation Is Not Important

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- There are two common cases where correlation can be ignored:
 - Source resistance R_s is **small** compared to input resistance $R_i \rightarrow$ i.e., voltage source input
 - Source resistance R_s is **large** compared to input resistance $R_i \rightarrow$ i.e., current source input

1) $R_s = \text{small}$ (ideally = 0 for an ideal voltage source):

\therefore For $R_s = \text{small}$, i_{eq}^2 can be neglected \rightarrow only v_{eq}^2 is important!
 (Thus, we need not deal with correlation)

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Cases Where Correlation Is Not Important

2) $R_S = \text{large}$ (Ideally = ∞ for an ideal current source)

Voltage v_{eq}^2 effectively "opened" out!

$$v_i = \frac{R_{in}}{\infty + R_{in}} v_{eq} = 0!$$

\therefore For $R_S = \text{large}$, v_{eq}^2 can be neglected!
 \rightarrow only i_{eq}^2 is important!
 (... and again, we need not deal with correlation)

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LF356 Op Amp Data Sheet

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LF155/LF156/LF256/LF257/LF355/LF356/LF357 JFET Input Operational Amplifiers

General Description
 These are the first monolithic JFET input operational amplifiers to incorporate well matched, high voltage JFETs on the same chip with standard bipolar transistors (BI-FET™ Technology). These amplifiers feature low input bias and offset currents/low offset voltage and offset voltage drift, coupled with offset adjust which does not degrade drift or common-mode rejection. The devices are also designed for high slew rate, wide bandwidth, extremely fast settling time, low voltage and current noise and a low 1/f noise corner.

Common Features

- Logarithmic amplifiers
- Photocell amplifiers
- Sample and Hold circuits
- Low input bias current: 30pA
- Low input Offset Current: 3pA
- High input impedance: $10^{12}\Omega$
- Low input noise current: $0.61 \text{ pA}/\sqrt{\text{Hz}}$
- Low common-mode rejection ratio: 100 dB
- Large dc voltage gain: 106 dB

Features

Advantages

- Replace expensive hybrid and module FET op amps
- Rugged JFETs allow blow-out free handling compared with MOSFET input devices
- Excellent for low noise applications using either high or low source impedance—very low 1/f corner
- Offset adjust does not degrade drift or common-mode rejection as in most monolithic amplifiers
- New output stage allows use of large capacitive loads (5,000 pF) without stability problems
- Internal compensation and large differential input voltage capability

Uncommon Features

	LF155/ LF355	LF156/ LF256/ LF356	LF257/ LF357	Units
Extremely fast settling time to 0.01%	4	1.5	1.5	μs
Fast slew rate	5	12	50	V/ μs
Wide gain bandwidth	2.5	5	20	MHz
Low input noise	20	12	12	nV/ $\sqrt{\text{Hz}}$

Applications

- Precision high speed integrators
- Fast D/A and A/D converters
- High impedance buffers
- Wideband, low noise, low drift amplifiers

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Example ARW Calculation

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Example Design:

Sensor Element:

- $m = (100\mu\text{m})(100\mu\text{m})(20\mu\text{m})(2300\text{kg}/\text{m}^3) = 4.6 \times 10^{-10}\text{kg}$
- $\omega_s = 2\pi(15\text{kHz})$
- $\omega_d = 2\pi(10\text{kHz})$
- $k_s = \omega_s^2 m = 4.09 \text{ N/m}$
- $x_d = 20 \mu\text{m}$
- $Q_s = 50,000$
- $V_p = 5\text{V}$
- $h = 20 \mu\text{m}$
- $d = 1 \mu\text{m}$

Sensing Circuitry:

- $R_f = 100\text{k}\Omega \rightarrow 1\text{M}\Omega$
- $i_{ia} = 0.01 \text{ pA}/\sqrt{\text{Hz}}$
- $v_{ia} = 12 \text{ nV}/\sqrt{\text{Hz}}$

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Example ARW Calculation (cont)

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Get rotation rate to output current scale factor:

$$A = 2 \frac{\omega_d Q_s x_d \eta_e}{\omega_s} |\Theta(j\omega_d)| = 2 \left(\frac{10\text{k}}{15\text{k}} \right) (50\text{k}) (20\mu\text{m}) (5) (2000\epsilon_0) (0.000024) = 2.83 \times 10^{-12} \text{C}$$

$$\Theta(j\omega_d) = \frac{(j\omega_d)(\omega_s/\omega_s)}{-\omega_d^2 + j\omega_d \frac{\omega_s}{Q_s} + \omega_s^2} = \frac{j(10\text{k})(15\text{k})/(50\text{k})}{(15\text{k})^2 - (10\text{k})^2 + j(10\text{k})(15\text{k})/50\text{k}} = \frac{j(3\text{k})}{1.25 \times 10^8 + j(3\text{k})}$$

$$\rightarrow |\Theta(j\omega_d)| = \frac{3\text{k}}{\sqrt{(1.25 \times 10^8)^2 + (3\text{k})^2}} = 0.000024 \text{ } 8.854 \times 10^{-12} \text{ F/m}$$

$$\frac{\partial C}{\partial x} = \frac{C_0}{d} = \frac{\epsilon_0 h \eta_e}{d} = \frac{\epsilon_0 (20\mu\text{m})(100\mu\text{m})}{(1\mu\text{m})^2} = 2000\epsilon_0 \rightarrow \eta_e = V_p \frac{\partial C}{\partial x} = 5(2000\epsilon_0) = 8.854 \times 10^{-12} \text{ F/m}$$

Assume electrode covers the whole sidewall.

Then, get noise:

$$\frac{\overline{\log_{10}}}{\Delta f} = \frac{4kT}{R_x} |\Theta(j\omega_d)|^2 + \frac{4kT}{R_f} + \frac{\overline{i_{ia}}}{\Delta f} + \frac{\overline{v_{ia}}}{\Delta f} \left(\frac{1}{R_f} \right)$$

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Example ARW Calculation (cont)

$$R_x = \frac{\omega_s m}{Q_s \eta_e} = \frac{2\pi(15K)(4.6 \times 10^{-10})}{(50K)(8.85 \times 10^{-12})} = 110.6 k\Omega$$

$$\frac{i_{eqTOT}^2}{\Delta f} = \frac{(1.66 \times 10^{-29})}{(110.6K)} (0.000024)^2 + \frac{(1.66 \times 10^{-29})}{1M} + (0.01p)^2 + \frac{(12n)^2}{(1M)^2}$$

$8.64 \times 10^{-35} A^2/Hz$ (Sensor element noise insignificant)
 $1.66 \times 10^{-26} A^2/Hz$ (Noise from R_f dominates!)
 $1 \times 10^{-28} A^2/Hz$
 $1.44 \times 10^{-28} A^2/Hz$

$$\therefore \frac{i_{eqTOT}^2}{\Delta f} = 1.68 \times 10^{-26} A^2/Hz \rightarrow i_{eqTOT} = \sqrt{\frac{i_{eqTOT}^2}{\Delta f}} = 1.30 \times 10^{-13} A/\sqrt{Hz}$$

$$\therefore \Omega_{min} = \frac{i_{eqTOT}}{A} \left(\frac{3600s}{hr} \right) \left(\frac{180^\circ}{\pi} \right) = \frac{1.30 \times 10^{-13}}{2.83 \times 10^{-12}} (3600) \left(\frac{180}{\pi} \right) = 9448 (\%/hr)/\sqrt{Hz}$$

And finally:
 $ARW = \frac{1}{60} \Omega_{min} = \frac{1}{60} (9448) = 157 \%/hr = ARW \Rightarrow$ Almost turned around in 1 hour!

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What if $\omega_d = \omega_s$?

If $\omega_d = \omega_s = 15KHz$, then $|G(j\omega_d)| = 1$ and

$$A = Z \frac{\omega_d}{\omega_s} Q_s \chi_d \eta_e |G(j\omega_d)| = Z Q_s \chi_d \eta_e = 2(50K)(20\mu)(5)(2000\epsilon_0) = 1.77 \times 10^{-7} C$$

$$\frac{i_{eqTOT}^2}{\Delta f} = \frac{(1.66 \times 10^{-29})}{(110.6K)} (1)^2 + \frac{(1.66 \times 10^{-29})}{1M} + (0.01p)^2 + \frac{(12n)^2}{(1M)^2}$$

$1.51 \times 10^{-25} A^2/Hz$
 $1.66 \times 10^{-26} A^2/Hz$
 $1 \times 10^{-28} A^2/Hz$
 $1.44 \times 10^{-28} A^2/Hz$

Now, the sensor element dominates!

$$\therefore \frac{i_{eqTOT}^2}{\Delta f} = 1.67 \times 10^{-25} A^2/Hz \rightarrow i_{eqTOT} = \sqrt{\frac{i_{eqTOT}^2}{\Delta f}} = 4.08 \times 10^{-13} A/\sqrt{Hz}$$

$$\therefore \Omega_{min} = \frac{i_{eqTOT}}{A} \left(\frac{3600s}{hr} \right) \left(\frac{180^\circ}{\pi} \right) = \frac{4.08 \times 10^{-13}}{1.77 \times 10^{-7}} (3600) \left(\frac{180}{\pi} \right) = 0.476 (\%/hr)/\sqrt{Hz}$$

And finally:
 $ARW = \frac{1}{60} \Omega_{min} = \frac{1}{60} (0.476) = 0.0079 \%/hr = ARW \Rightarrow$ Navigation grade!

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